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				Filing Date		July 16, 2003			
				First Named Inventor:		Aaditya Mahajan			
				Examiner name: unknown		GROUP: unknown			
Sheet	1	of	1	Attorney Docket Number		TRQ-12957			
<b>U.S. PUBLISHED PATENT APPLICATIONS</b>									
Examiner Initials*	Cited No. <sup>1</sup>	U.S. Patent Document Number      Kind Code <sup>2</sup> (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines Where Relevant Info. Appear	
<b>U.S. PATENT DOCUMENTS</b>									
Examiner Initials*	Cited No. <sup>1</sup>	U.S. Patent Document Number      Kind Code <sup>2</sup> (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY		Pages, Columns, Lines Where Relevant Info. Appear	
<b>FOREIGN PATENT DOCUMENTS</b>									
Examiner Initials*	Cited No. <sup>1</sup>	Foreign Patent Document Office <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)			Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T <sup>6</sup>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>									
Bollaert et al., "Metamorphic In <sub>0.4</sub> Al <sub>0.6</sub> As/In <sub>0.4</sub> Ga <sub>0.6</sub> As HEMT's on GaAs Substrate", IEEE Electron Device Letters, Vol. 20, No. 3, March 1999, pp. 123-125.									
Dumka et al., "High Performance 0.35 μm Gate-Length Monolithic Enhancement/Depletion-Mode Metamorphic In <sub>0.52</sub> Al <sub>0.48</sub> As/In <sub>0.53</sub> Ga <sub>0.47</sub> As HEMTs on GaAs Substrates", IEEE Electron Device Letters, Vol. 22, No. 8, August 2001, pp. 364-366.									
Hoke et al., "Molecular Beam Epitaxial Growth And Device Performance Of Metamorphic High Electron Mobility Transistor Structures", J. Vac. Sci. Technol. B, Vol. 17, No. 3, May/Jun 1999, pp. 1131-1135.									
Jang et al., "Long Wavelength Metamorphic Double Heterojunction In <sub>0.53</sub> Ga <sub>0.47</sub> As/InAlGaAs/In <sub>0.52</sub> Al <sub>0.48</sub> As Photodiodes On GaAs Substrates", Electronics Letters, Vol. 37, No. 11, May 24, 2001.									
Jang et al., "The Impact Of A Large Bandgap Drift Region In Long-Wavelength Metamorphic Photodiodes", IEEE Photonics Technology letters, Vol. 13, No. 10, October 2001, pp. 1097-1099.									
Jang et al., "Long-Wavelength In <sub>0.53</sub> Ga <sub>0.47</sub> As Metamorphic p-i-n Photodiodes On GaAs Substrates", IEEE Photonics Technology Letters, Vol. 13, No. 2, February 2001, pp. 151-153.									
Zaknounge et al., "InAlAs/InGaAs Metamorphic HEMT With High Current Density And High Breakdown Voltage", IEEE Electron Device Letters, vol. 19, No. 9, September 1998, pp. 345-347.									
EXAMINER					DATE CONSIDERED				

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